



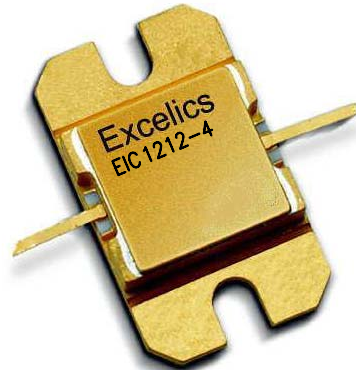
EIC1212-4

ISSUED DATE: 09/20//2007

12.20-12.70 GHz 4-Watt Internally Matched Power FET

FEATURES

- 12.20-12.70GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 6.5dB Power Gain at 1dB Compression
- 28% Power Added Efficiency
- -46 dBc IM3 at PO = 25.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 12.20-12.70GHz	35.5	36.5		dBm
G _{1dB}	Gain at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 12.20-12.70GHz	5.5	6.5		dB
ΔG	Gain Flatness V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 12.20-12.70GHz			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 1100mA f = 12.20-12.70GHz		28		%
I _{d1dB}	Drain Current at 1dB Compression f = 12.20-12.70GHz		1100	1300	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; P _{out} = 25.5 dBm S.C.L. ² V _{DS} = 10 V, I _{DSQ} ≈ 65% IDSS f = 12.70GHz	-43	-46		dBc
I _{DSS}	Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V		2000	2500	mA
V _P	Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 20 mA		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		5.5	6.0	°C/W

- Note: 1. Tested with 100 Ohm gate resistor.
 2. S.C.L. = Single Carrier Level.
 3. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V _{ds}	Drain-Source Voltage	15V	10V
V _{gs}	Gate-Source Voltage	-5V	-4V
I _{gsf}	Forward Gate Current	48mA	14.4mA
I _{gsr}	Reverse Gate Current	-9.6mA	-2.4mA
P _{in}	Input Power	35.5dBm	@ 3dB Compression
T _{ch}	Channel Temperature	175C	175C
T _{stg}	Storage Temperature	-65C to +175C	-65C to +175C
P _t	Total Power Dissipation	25W	25W

- Note: 1. Exceeding any of the above ratings may result in permanent damage.
 2. Exceeding any of the above ratings may reduce MTTF below design goals.

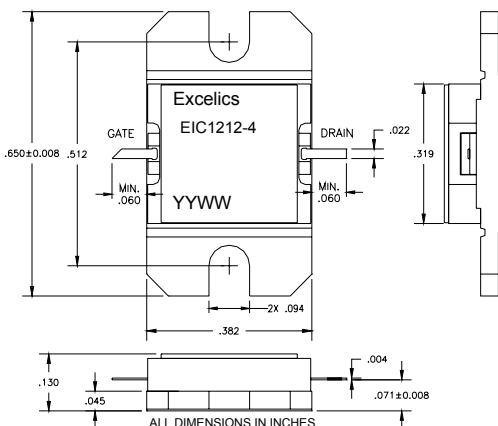
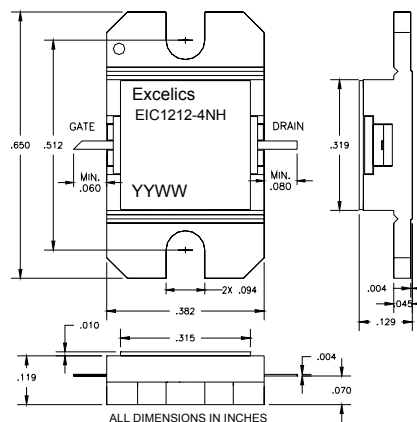
Specifications are subject to change without notice.

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PACKAGES OUTLINE

 Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

EIC1212-4 (Hermetic)

Caution! ESD sensitive device.
EIC1212-4NH (Non-Hermetic)

Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC1212-4	Hermetic	Industrial	12.20-12.70GHz	35.5	-43
EIC1212-4NH	Non-Hermetic	Industrial	12.20-12.70GHz	35.5	-43

 Notes: 1. Contact factory for military and hi-rel grades.
 2. Exact test conditions are specified in "Electrical Characteristics" table.

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